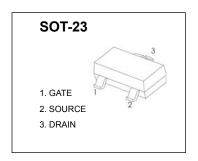


## JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

# **SOT-23 Plastic-Encapsulate MOSFETS**

# CJ2305 P-Channel MOSFET

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> MAX	I <sub>D</sub>
	45mΩ@-4.5V	
-12 V	60mΩ@-2.5V	-4.1A
	90mΩ@-1.8V	



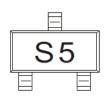
## **FEATURE**

• TrenchFET Power MOSFET

#### **APPLICATION**

- Load Switch for Portable Devices
- DC/DC Converter

#### **MARKING**



## **Equivalent Circuit**



## Maximum ratings (T<sub>a</sub>=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DS</sub>	-12	V	
Gate-Source Voltage	$V_{GS}$	±8	V	
Continuous Drain Current	I <sub>D</sub>	-4.1	^	
Continuous Source-Drain Diode Current	Is	-0.8	Α	
Maximum Power Dissipation	P <sub>D</sub>	0.35	W	
Thermal Resistance from Junction to Ambient(t≤10s)	$R_{\theta JA}$	357	°C/W	
Junction Temperature	TJ	150	°C	
Storage Temperature	T <sub>STG</sub>	-50 ~+150		

## **MOSFET ELECTRICAL CHARACTERISTICS**

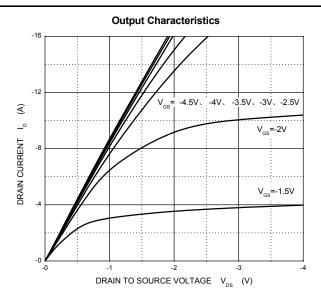
 $T_a$ =25  $^{\circ}$ C unless otherwise specified

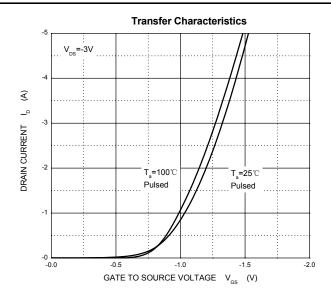
Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Static						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =-250µA	-12			V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.5		-0.9	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V			±100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =-8V, V <sub>GS</sub> =0V			-1	μA
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.5A		30	45	
Drain-source on-state resistance	RDS(on)	V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-3A		40	60	mΩ
		V <sub>GS</sub> =-1.8V,I <sub>D</sub> =-2.0A		60	90	
Forward transconductance <sup>a</sup>	<b>g</b> fs	V <sub>DS</sub> =-5V, I <sub>D</sub> =-4.1A	6			S
Dynamic	- 1		•	•	•	•
Input capacitance <sup>b,c</sup>	C <sub>iss</sub>			740		
Output capacitance <sup>b,c</sup>	C <sub>oss</sub>	V <sub>DS</sub> =-4V,V <sub>GS</sub> =0V,f =1MHz		290		pF
Reverse transfer capacitance <sup>b,c</sup>	C <sub>rss</sub>	_		190		
	Qg	V <sub>DS</sub> =-4V,V <sub>GS</sub> =-4.5V,		7.8	15	nC
Total gate charge <sup>b</sup>		I <sub>D</sub> =-4.1A				
		V <sub>DS</sub> =-4V,V <sub>GS</sub> =-2.5V,		4.5	9	
Gate-source charge <sup>b</sup>	$Q_{gs}$	VDS4V,VGS2.5V,		1.2		
Gate-drain charge <sup>b</sup>	$Q_{gd}$	- 104. IA		1.6		
Gate resistance <sup>b,c</sup>	$R_g$	f=1MHz	1.4		14	Ω
Turn-on delay time <sup>b,c</sup>	td(on)	V 0/		13	20	
Rise time <sup>b,c</sup>	tr	V <sub>DD</sub> =-4V, R <sub>L</sub> =1.2Ω, I <sub>D</sub> ≈-3.3A,		35	53	ns
Turn-off Delay time <sup>b,c</sup>	td(off)	- R <sub>L</sub> =1.2Ω, ID ≈-3.3A, - V <sub>GEN</sub> =-4.5V,Rg=1Ω		32	48	
Fall time <sup>b,c</sup>	tf	VGEN4.5V,NG-122		10	20	
Turn-on delay time <sup>b,c</sup>	td(on)			5	10	
Rise time <sup>b,c</sup>	tr	V <sub>DD</sub> =-4V,		11	17	
Turn-off delay time <sup>b,c</sup>	td(off)	- R <sub>L</sub> =1.2Ω, I <sub>D</sub> ≈-3.3A,		22	33	1
Fall time <sup>b,c</sup>	tf	$V_{\text{GEN}}$ =-8V,Rg=1 $\Omega$		16	24	
Drain-source body diode characteristic	S		•	•	•	
Continuous source-drain diode current	Is	T <sub>C</sub> =25℃			-1.4	Α.
Pulse diode forward current <sup>a</sup>	I <sub>SM</sub>				-10	- A
Body ciode voltage	$V_{SD}$	I <sub>F</sub> =-3.3A			-1.2	V

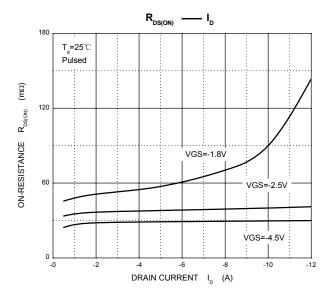
### Note:

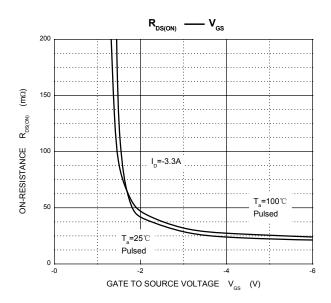
- a. Pulse Test ; Pulse Width ≤300μs, Duty Cycle ≤2%.
- b. Guaranteed by design, not subject to production testing.
- c. These parameters have no way to verify.

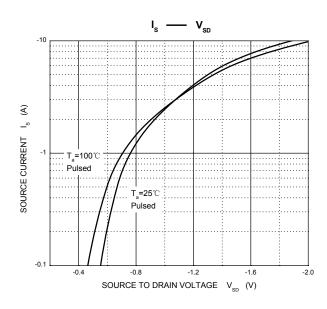
## **Typical Characteristics**

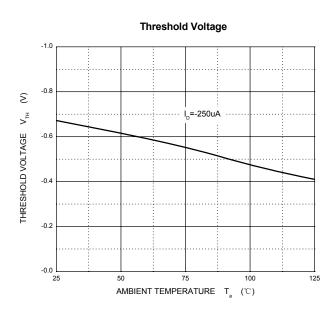




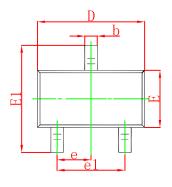


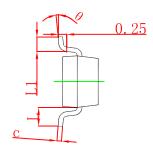


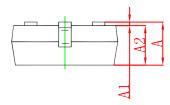




## **SOT-23 Package Outline Dimensions**

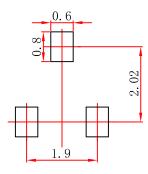






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550	REF	0.022	REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

## **SOT-23 Suggested Pad Layout**



#### Note:

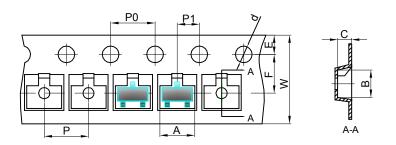
- 1. Controlling dimension: in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

#### NOTICE

JCET reserve the right to make modifications,enhancements, improvements, corrections or other changes without further notice to any product herein.JCET does not assume any liability arising out of the application or use of any product described herein.

# SOT-23 Tape and reel

## SOT-23 Embossed Carrier Tape

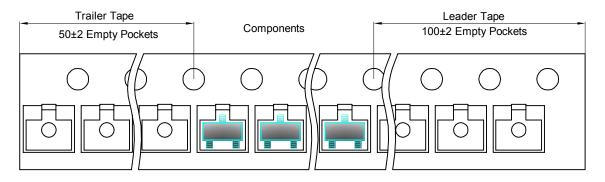


#### Packaging Description:

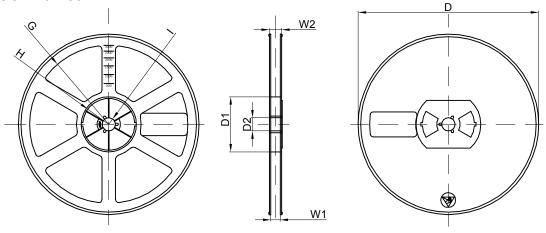
SOT-23 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 17.8cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type A B C d E F P0 P P1 W								W		
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

## SOT-23 Tape Leader and Trailer







	Dimensions are in millimeter									
Reel Option D D1 D2 G H I W1 W2								W2		
7"Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30		

REEL	Reel Size	Вох	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	